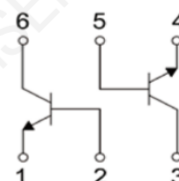
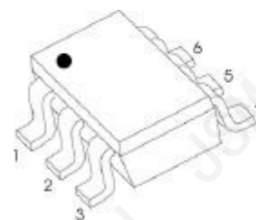


Features

- ◆ Two transistors in one package
- ◆ Reduces number of components and board space
- ◆ No mutual interference between the transistors



Equivalent Circuit

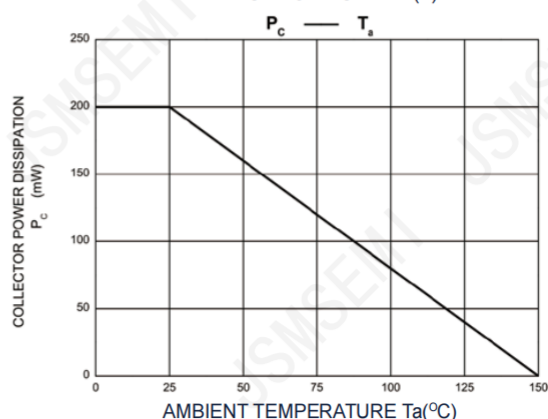
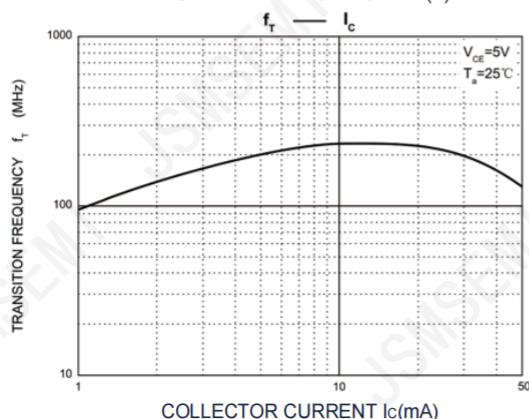
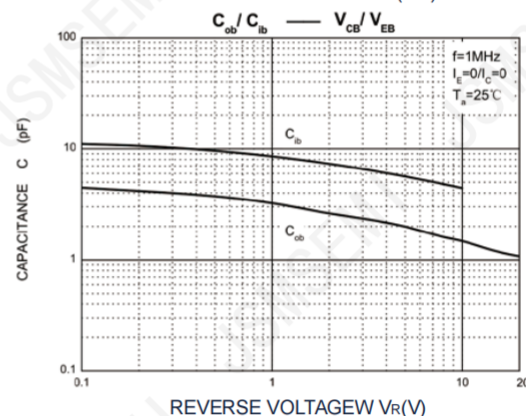
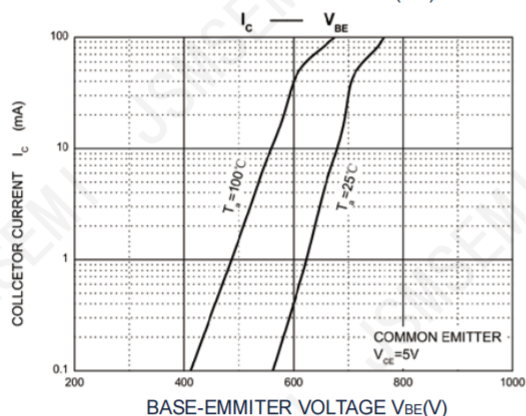
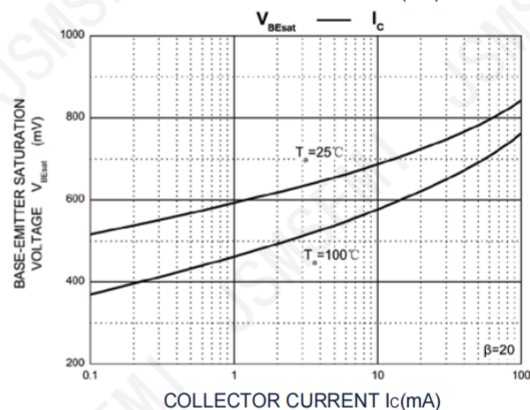
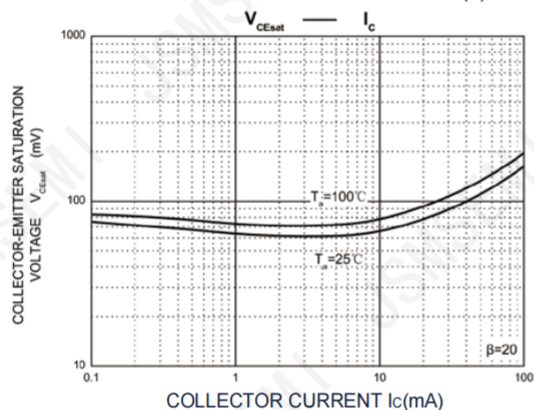
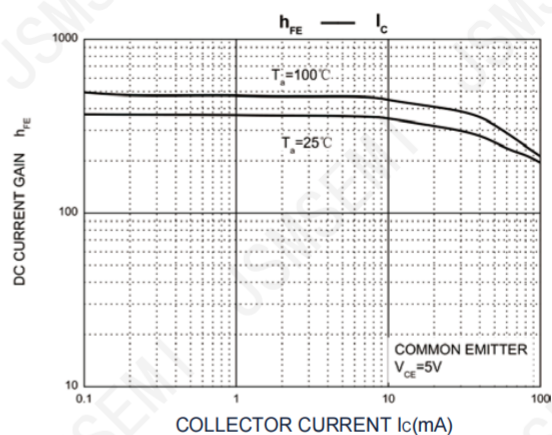
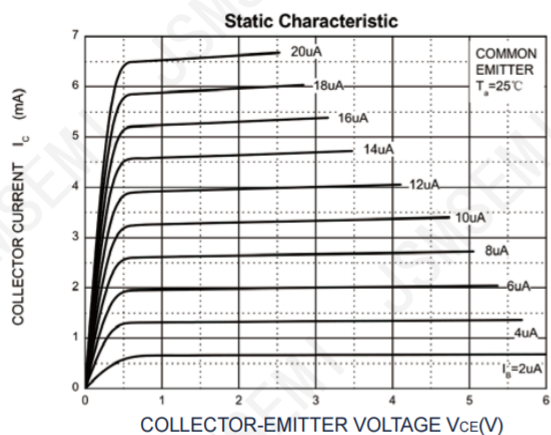
Absolute Maximum Ratings(TA=25℃)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	80	V
V _{CEO}	Collector-Emitter Voltage	65	V
V _{EBO}	Emitter-Base Voltage	6	V
I _C	Collector Current	0.1	A
P _C	Collector Power Dissipation	0.2	W
T _J , T _{stg}	Operation Junction And Storage Temperature Range	-55 ~ +150	℃

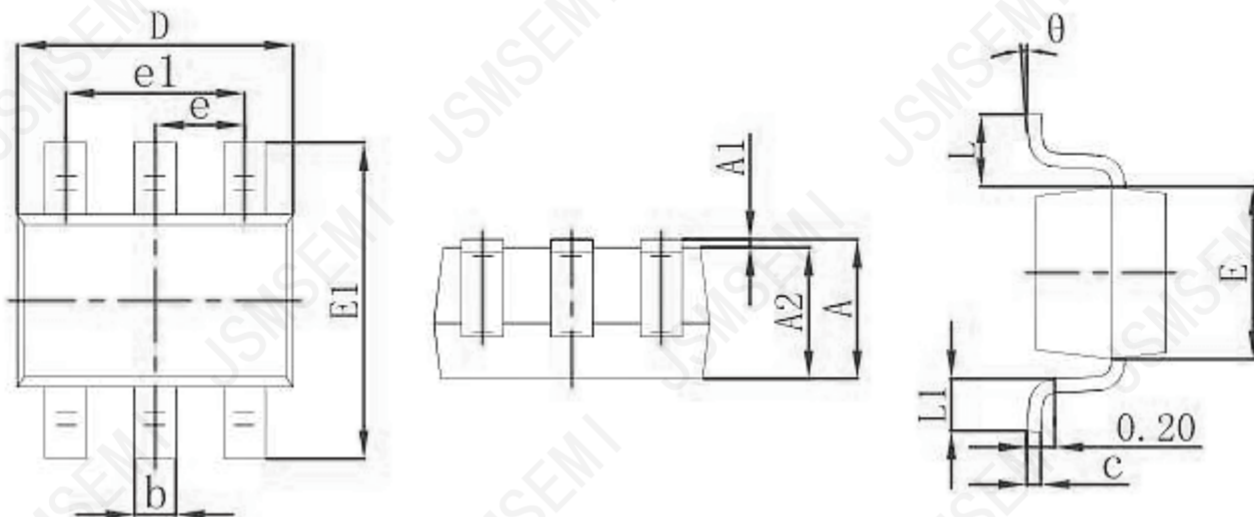
Electrical Characteristics (TA=25℃ unless otherwise specified)

Symbol	Parameter	Test conditions	Min	Typ	Max	Unit
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =10μA, I _E =0	80			V
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =10mA, I _B =0	65			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =10μA, I _C =0	6			V
I _{CBO}	Collector cut-off current	V _{CB} =30V, I _E =0			15	nA
I _{EBO}	Emitter cut-off current	V _{EB} =5V, I _C =0			500	nA
h _{FE}	DC current gain	V _{CE} =5V, I _C =2mA	200		450	
V _{CE(sat)}	Collector-emitter saturation voltage	I _C =10mA, I _B =0.5mA			0.1	V
		I _C =100mA, I _B =5mA			0.3	V
V _{BE(sat)}	Base-emitter saturation voltage	I _C =10mA, I _B =0.5mA		0.77		V
f _T	Transition frequency	V _{CB} =5V, I _E =10mA, f=100MHz	100			MHz
C _{obo}	Base-emitter saturation voltage	V _{CB} =10V, I _E =0A, f=1MHz			1.5	pF

Typical Characteristics



Package Outline Dimensions



Symbol	Dimensions in Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.150	0.350	0.006	0.014
c	0.100	0.150	0.004	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.450	0.085	0.096
e	0.650 TYP		0.026 TYP	
e1	1.200	1.400	0.047	0.055
L	0.525 REF		0.021 REF	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°

Revision History

Rev.	Change	Date
V1.0	Initial version	2/23/2024

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